



# European Library-based flow of Embedded Silicon test Instruments

ELESIS final review  
December 2015



## Goal & Technology

**Goal:** Tools to support methods for qualifying dependability sensors IP in System-On-Chip

**Method:** New software comprising a model driven, statistical simulation approach with build-in dependability IP database.

**A tool to assess the quality and sustained performance of SoC's over operational lifetime**

## Dependability Model Simulator - DMS

**ELESIS exploitation & KPI's:** connecting project targets to customer key benefits with new DMS tool

### DMS: customer key benefit

Reduced **EDA integration time** for dependability features.

### ELESIS KPI

**TIME**

Advanced **sensor-in-SoC capability analysis** due to accurate model database

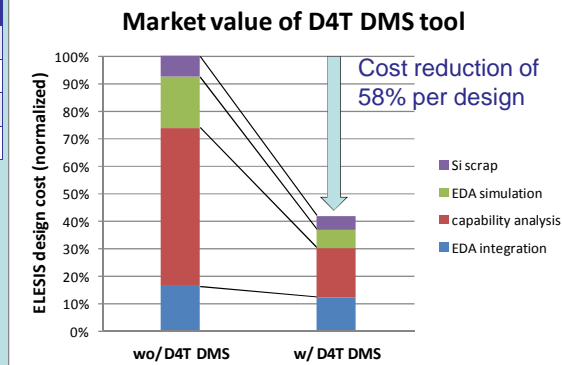
**QUALITY**

Reduced **"what-if" simulation effort** for dependability IP in SoC

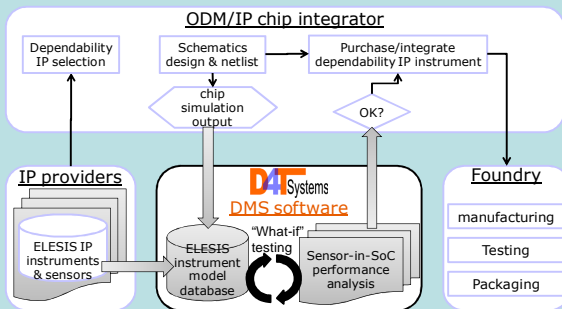
**TIME**

Reduced **wafer and silicon waste** by more efficient IP debug

**COST**



D4T Systems DMS tool is positioned at the pre-silicon design phase.



## ELESIS technology results: DMS software demonstration of dependability IP evaluation on AMS DUT

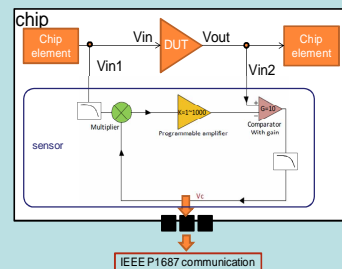
### Dependability Model Simulator demo:

Capability analysis on ELESIS sensor to monitor DC drift due to aging in SoC IP.

This dependability IP is evaluated on two devices with DMS:

- 1) General purpose OpAmp IP block for SoC's
- 2) High grade, robust OpAmp IP for SerDes high speed communication.

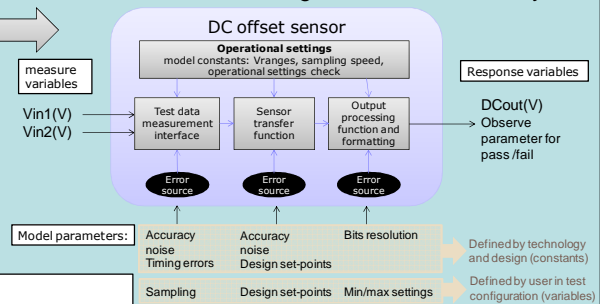
From transistor level circuit simulation to ....



### Dependability sensor:

- 1) DC offset drift due to NBTI.
- 2) DC offset sensed from AC signals through gain optimized loop

Model based design with statistical analysis



### IP model database

Workbench: sensor test and simulation setup

Database with libraries. The ELESIS instruments are implemented for two variants

The datasheet parameters as they will be used in the sensor model

User defined variables are defined and can vary per test

### Analysis: capability of dependability IP in SoC

DMS analysis output. Detected DC drift is displayed with statistical boundaries.

age (yr)	voff (mV)	std (mV)	Optimum K	NC curve
ip11	8.475	1.025	11.816	500
ip12	20.135	1.084	9.984	500
ip13	13.010	1.190	7.650	500
ip14	14.52	1.35	6.999	500
ip15	16.028	1.504	6.217	500
ip16	16.033	1.751	6.209	500
ip17	18.424	1.842	5.496	500

**ECSEL Joint Undertaking**

Electronic Components and Systems for European Leadership

For product pricing, services and technical information, please contact:

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